

High Current Surface Mount NPN Silicon Switching Transistor for Load Management in Portable Applications MMBT489LT1G

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	50	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	1.0	A
Collector Current – Peak	I_{CM}	2.0	A

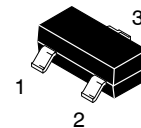
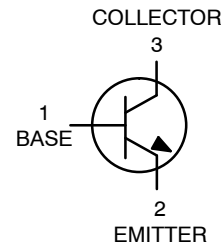
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	310 2.5	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	403	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	710 5.7	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	176	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Single Pulse < 10 s)	$P_{D\text{single}}$	575	mW
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

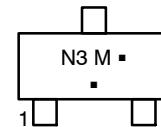
- FR-4 @ Minimum Pad
- FR-4 @ 1.0 X 1.0 inch Pad

30 VOLTS, 2.0 AMPERES NPN TRANSISTOR



SOT-23 (TO-236)
CASE 318
STYLE 6

MARKING DIAGRAM



N3 = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT489LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT489LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	30	–	Vdc
Collector – Base Breakdown Voltage ($I_C = 0.1\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	50	–	Vdc
Emitter – Base Breakdown Voltage ($I_E = 0.1\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	5.0	–	Vdc
Collector Cutoff Current ($V_{CB} = 30\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	0.1	μAdc
Collector – Emitter Cutoff Current ($V_{CES} = 30\text{ Vdc}$)	I_{CES}	–	0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 4.0\text{ Vdc}$)	I_{EBO}	–	0.1	μAdc

ON CHARACTERISTICS

DC Current Gain (Note 3) ($I_C = 50\text{ mA}$, $V_{CE} = 5.0\text{ V}$) ($I_C = 0.5\text{ A}$, $V_{CE} = 5.0\text{ V}$) ($I_C = 1.0\text{ A}$, $V_{CE} = 5.0\text{ V}$)	h_{FE}	300 300 200	– 900 –	
Collector – Emitter Saturation Voltage (Note 3) ($I_C = 1.0\text{ A}$, $I_B = 100\text{ mA}$) ($I_C = 0.5\text{ A}$, $I_B = 50\text{ mA}$) ($I_C = 0.1\text{ A}$, $I_B = 1.0\text{ mA}$)	$V_{CE(sat)}$	– – –	0.200 0.125 0.075	V
Base – Emitter Saturation Voltage (Note 3) ($I_C = 1.0\text{ A}$, $I_B = 0.1\text{ A}$)	$V_{BE(sat)}$	–	1.1	V
Base – Emitter Turn-on Voltage (Note 3) ($I_C = 1.0\text{ mA}$, $V_{CE} = 2.0\text{ V}$)	$V_{BE(on)}$	–	1.1	V
Cutoff Frequency ($I_C = 100\text{ mA}$, $V_{CE} = 5.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	100	–	MHz
Output Capacitance ($f = 1.0\text{ MHz}$)	C_{obo}	–	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulsed Condition: Pulse Width = 300 μsec , Duty Cycle $\leq 2\%$

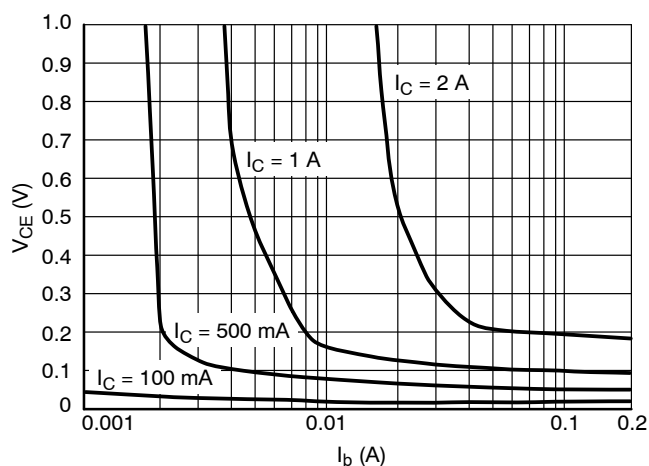


Figure 1. V_{CE} versus I_B

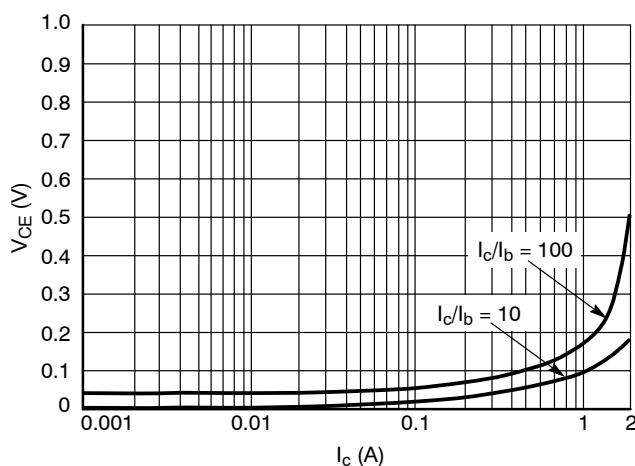


Figure 2. V_{CE} versus I_C

MMBT489LT1G

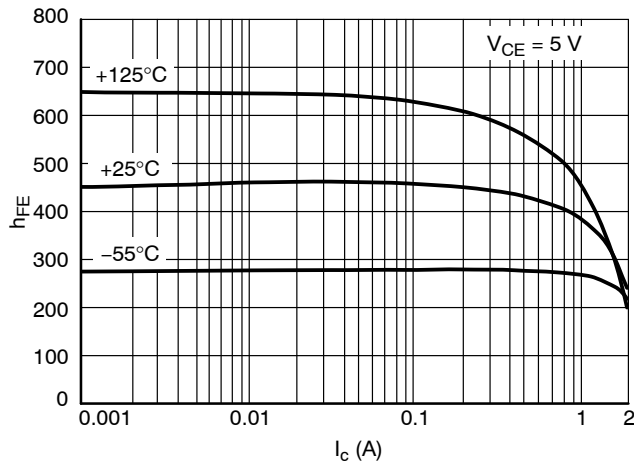


Figure 3. h_{FE} versus I_C

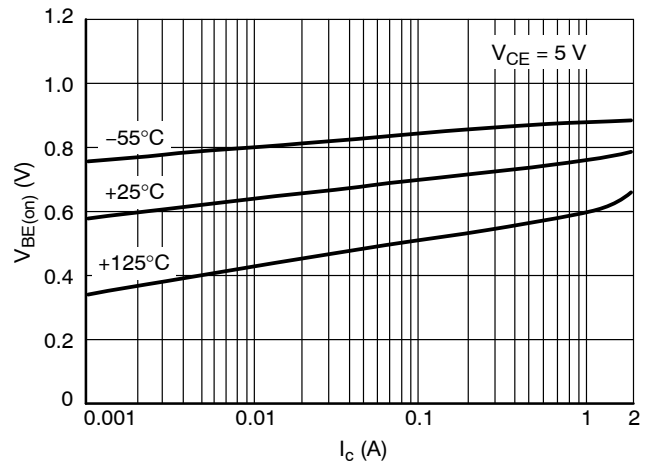


Figure 4. $V_{BE(on)}$ versus I_C

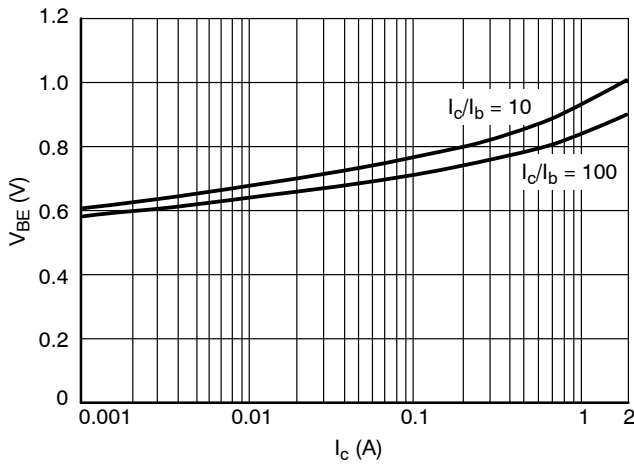


Figure 5. $V_{BE(sat)}$ versus I_C

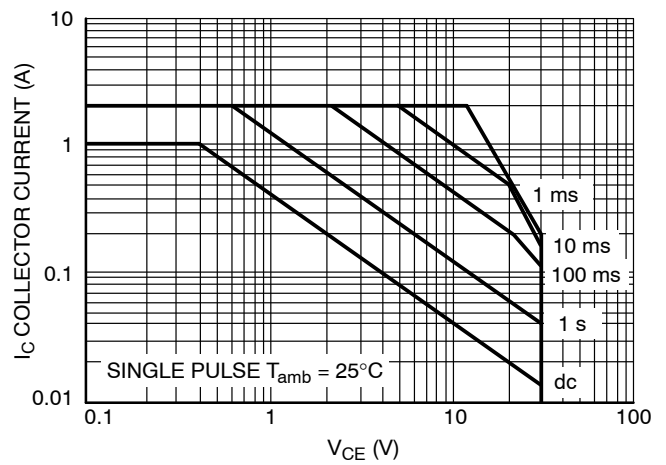


Figure 6. Safe Operating Area

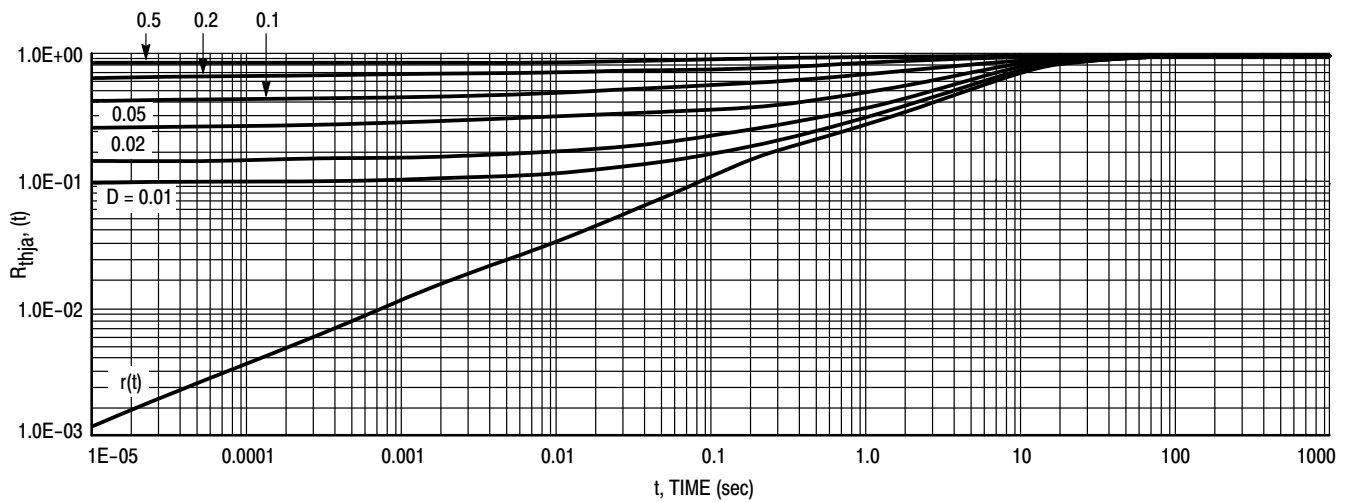
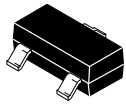


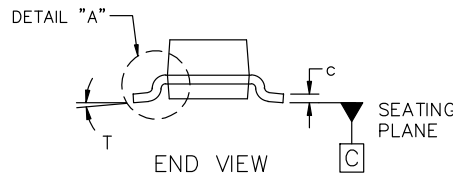
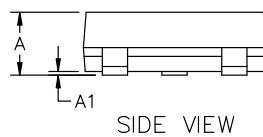
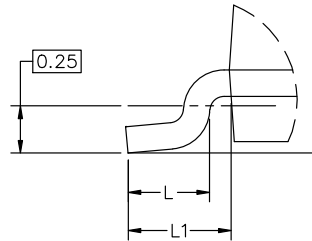
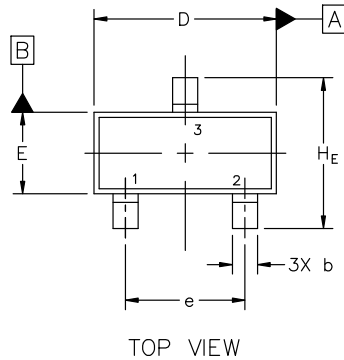
Figure 7. Normalized Thermal Response



SCALE 4:1

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CASE 318
ISSUE AU

DATE 14 AUG 2024

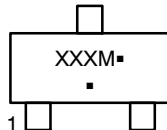


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

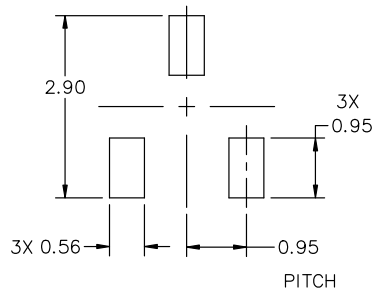
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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